

General Description:

HM3N100D , the silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-220F, which accords with the RoHS standard.

Features:

- I Fast Switching
- I Low ON Resistance($R_{DS(on)} \leq 6.0 \Omega$)
- I Low Gate Charge (Typical Data:19.7 nC)
- I Low Reverse transfer capacitances(Typical:2.2 pF)
- I 100% Single Pulse avalanche energy Test

Applications:

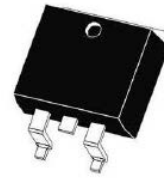
Electric welder、Inverter.

Absolute (Tc= 25°C unless otherwise specified):

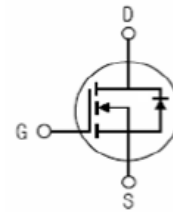
Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	1000	V
I_D	Continuous Drain Current	3	A
	Continuous Drain Current T _C = 100 °C	1.8	A
I_{DM}^{a1}	Pulsed Drain Current	12	A
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	30	mJ
dv/dt^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	30	W
	Derating Factor above 25°C	0.24	W/°C
T _J , T _{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	°C
T _L	Maximum Temperature for Soldering	300	°C

V_{DSS}	1000	V
I_D	3	A
$P_D(T_C=25^\circ\text{C})$	30	W
$R_{DS(ON)Typ}$	3.5	Ω

TO-263



Inner Equivalent Principium Chart



Electrical Characteristics (Tc= 25℃ unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Unit s
			Min.	Typ.	Max.	
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	1000	--	--	V
Δ BV _{DSS} / Δ T _J	Bvdss Temperature Coefficient	ID=250uA, Reference 25℃	--	1.24	--	V/℃
I _{DSS}	Drain to Source Leakage Current	V _{DS} =1000V, V _{GS} = 0V, T _a = 25℃	--	--	25	μA
		V _{DS} =960V, V _{GS} = 0V, T _a = 125℃	--	--	250	μA
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} =+30V	--	--	100	nA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} =-30V	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =1.5A	--	3.5	4.2	Ω
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	3.0	3.5	4.0	V
Pulse width tp ≤ 300μs, δ ≤ 2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g _{fs}	Forward Trans conductance	V _{DS} =15V, I _D =1.5A	--	5	--	S
R _g	Gate resistance	f = 1.0MHz	--	2.2	--	Ω
C _{iss}	Input Capacitance	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz	--	1006	--	pF
C _{oss}	Output Capacitance		--	59.8	--	
C _{rss}	Reverse Transfer Capacitance		--	2.2	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	I _D =3A V _{DD} = 600V R _G =10Ω	--	15.1	--	ns
t _r	Rise Time		--	19.4	--	
t _{d(OFF)}	Turn-Off Delay Time		--	25.6	--	
t _f	Fall Time		--	76.2	--	
Q _g	Total Gate Charge	I _D =3A V _{DD} =960V V _{GS} = 10V	--	19.7	--	nC
Q _{gs}	Gate to Source Charge		--	7.5	--	
Q _{gd}	Gate to Drain ("Miller")Charge		--	5.4	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I _S	Continuous Source Current (Body Diode)		--	--	3	A
I _{SM}	Maximum Pulsed Current (Body Diode)		--	--	12	A
V _{SD}	Diode Forward Voltage	I _S =3.0A,V _{GS} =0V	--	--	1.5	V
trr	Reverse Recovery Time	I _S =3.0A,T _j = 25 °C dI _F /dt=100A/us, V _{GS} =0V	--	526	--	ns
Q _{rr}	Reverse Recovery Charge		--	2000	--	nC
I _{R_{RM}}	Reverse Recovery Current		--	9	--	A
Pulse width tp≤300μs, δ ≤2%						

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Junction-to-Case	4.2	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	62.5	$^\circ C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L=10mH, I_D=2.5A, \text{Start } T_J=25^\circ C$

^{a3}: $I_{SD}=3A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}, \text{Start } T_J=25^\circ C$

Characteristics Curve:

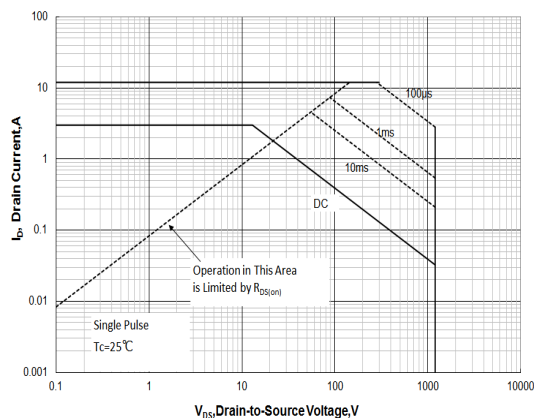


Figure 1 Maximum Forward Bias Safe Operating Area

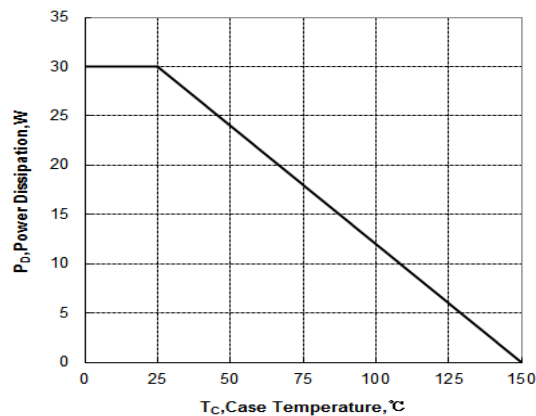


Figure 2 Maximum Power dissipation vs Case Temperature

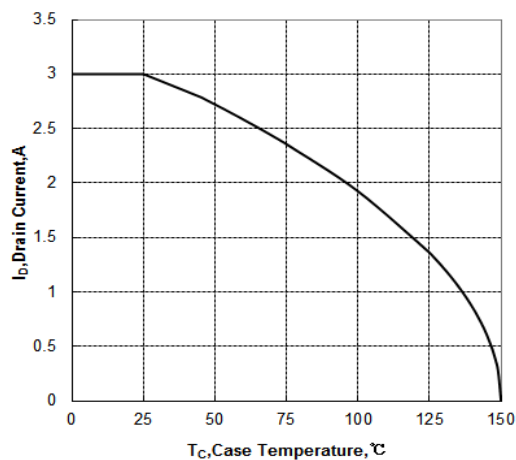


Figure 3 Maximum Continuous Drain Current vs Case Temperature

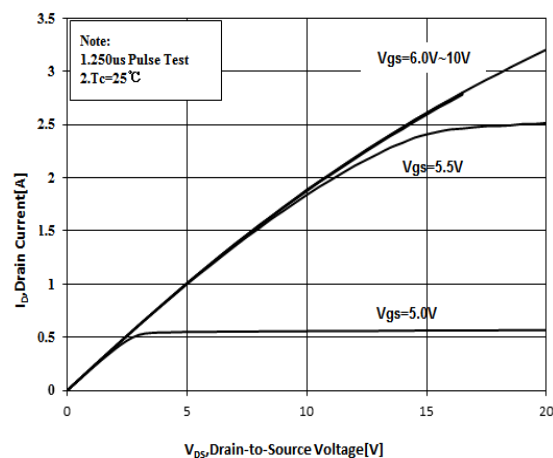


Figure 4 Typical Output Characteristics

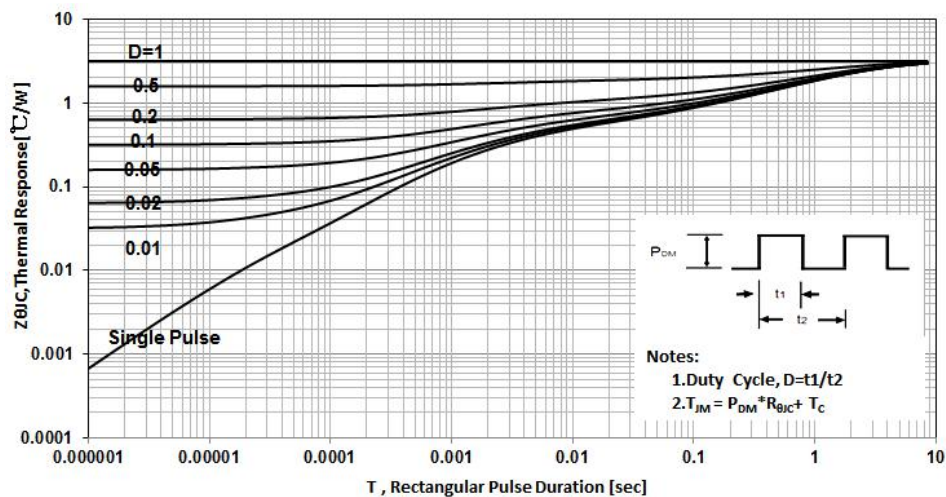


Figure 5 Maximum Effective Thermal Impedance , Junction to Case

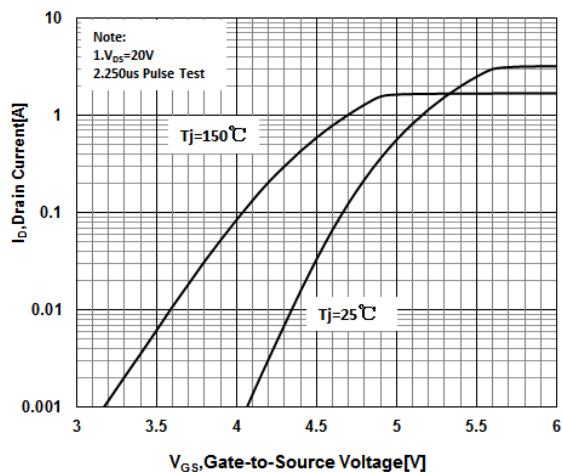


Figure 6 Typical Transfer Characteristics

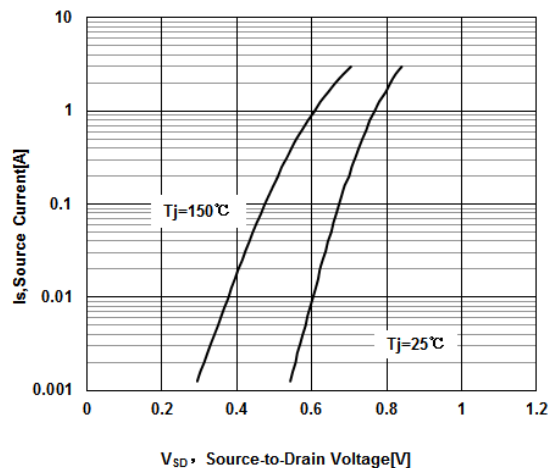


Figure 7 Typical Body Diode Transfer Characteristics

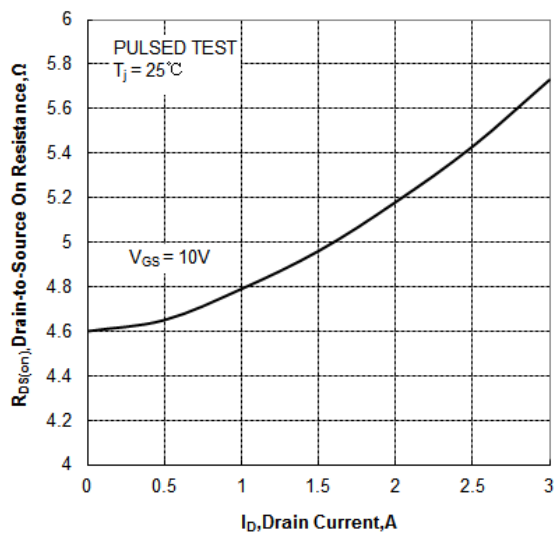


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

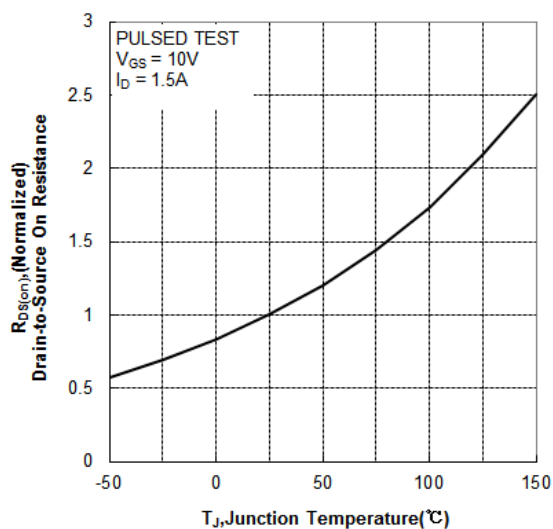


Figure 9 Typical Drain to Source on Resistance vs Junction Temperature

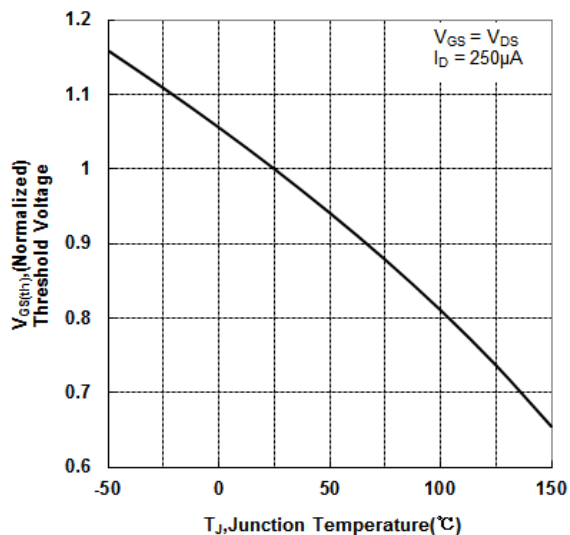


Figure 10 Typical Theshold Voltage vs Junction Temperature

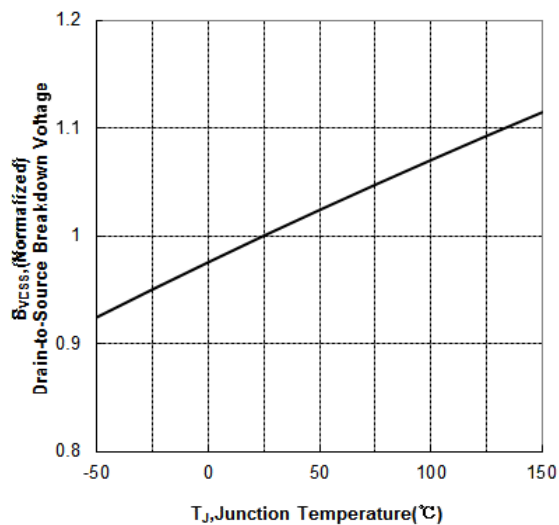


Figure 11 Typical Breakdown Voltage vs Junction Temperature

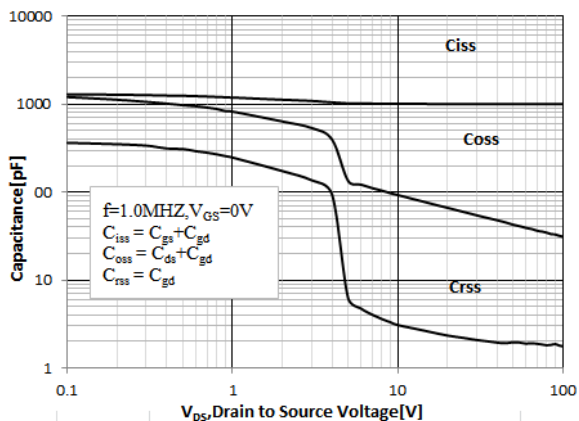


Figure 12 Typical Capacitance vs Drain to Source Voltage

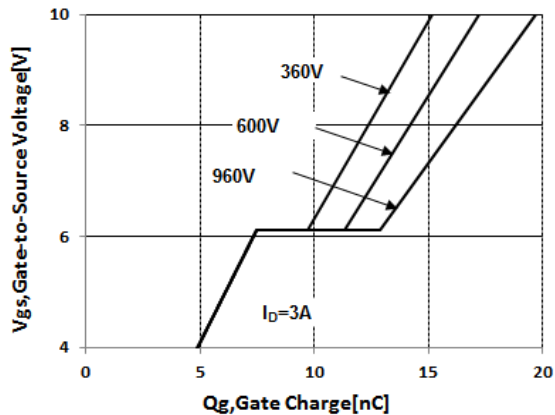


Figure 13 Typical Gate Charge vs Gate to Source Voltage

Test Circuit and Waveform:

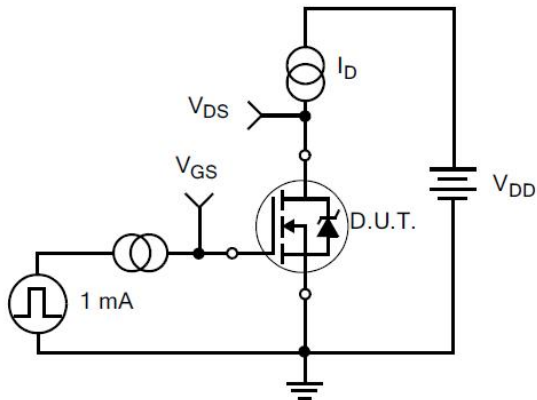


Figure 14. Gate Charge Test Circuit

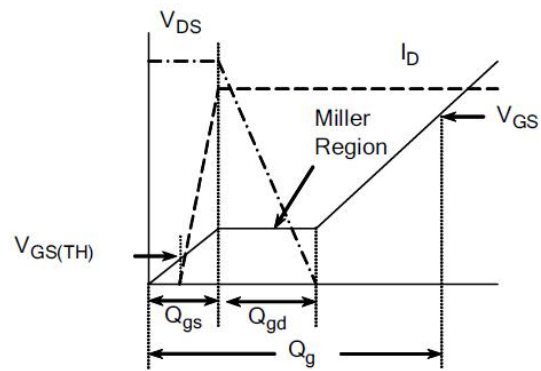


Figure 15. Gate Charge Waveforms

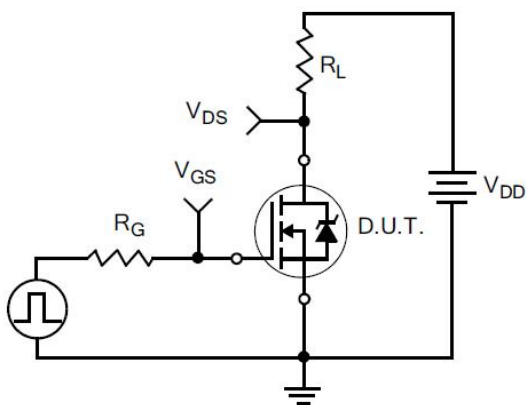


Figure 16. Resistive Switching Test Circuit

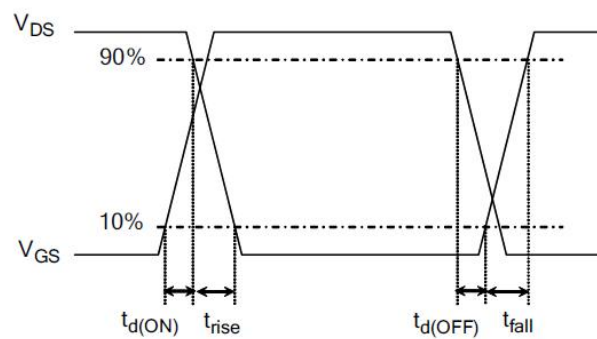


Figure 17. Resistive Switching Waveforms

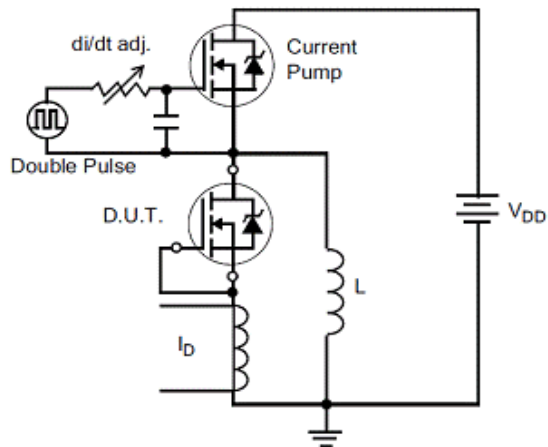


Figure 18. Diode Reverse Recovery Test Circuit

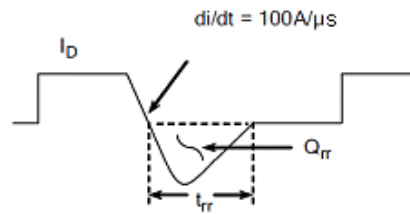


Figure 19. Diode Reverse Recovery Waveform

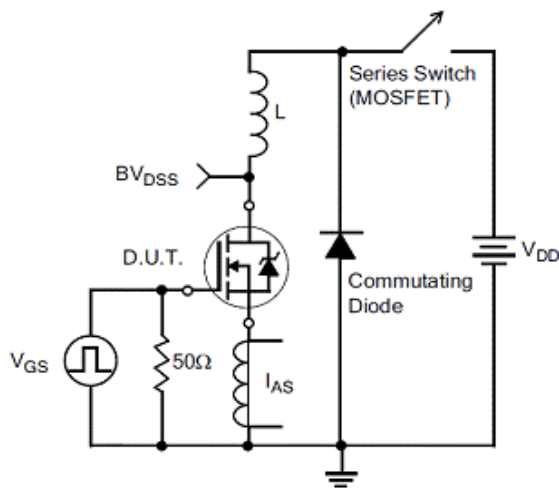


Figure20.Unclamped Inductive Switching Test Circuit

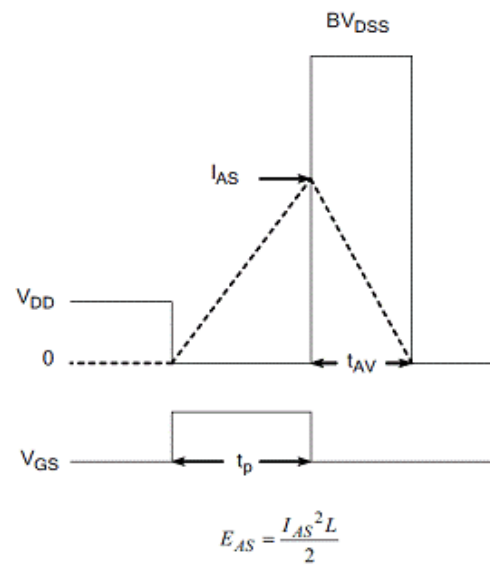
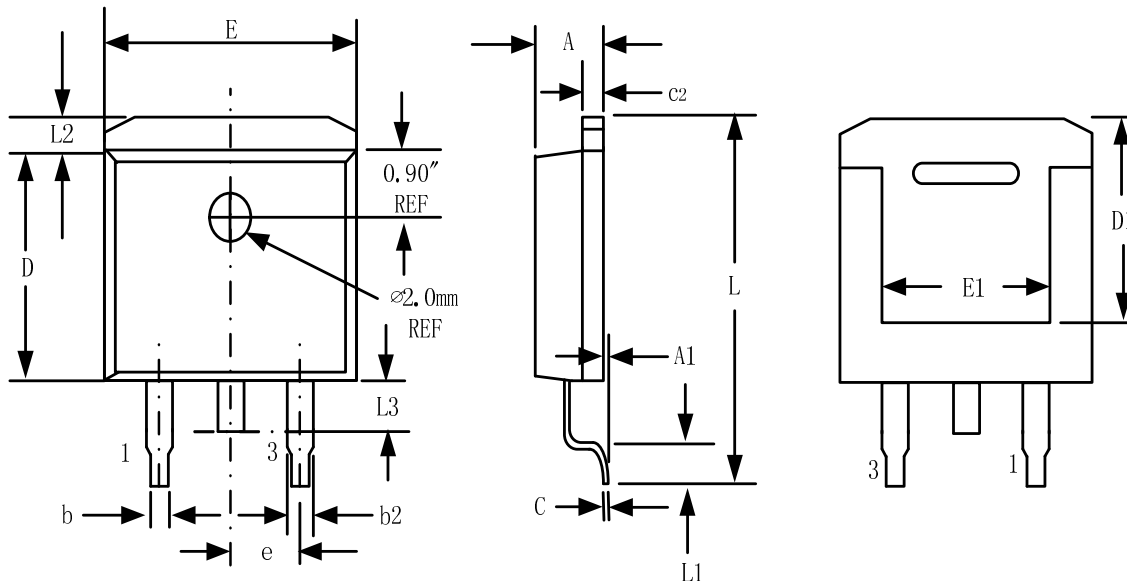


Figure21.Unclamped Inductive Switching Waveform

TO-263-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.57	0.170	0.180
A1	-	0.25		0.010
b	0.71	0.94	0.028	0.037
b2	1.15	1.40	0.045	0.055
c	0.46	0.61	0.018	0.024
c2	1.22	1.40	0.048	0.055
D	8.89	9.40	0.350	0.370
D1	8.01	8.23	0.315	0.324
E	10.04	10.28	0.395	0.405
E1	7.88	8.08	0.310	0.318
e	2.54 BSC		0.100 BSC	
L	14.73	15.75	0.580	0.620
L1	2.29	2.79	0.090	0.110
L2	1.15	1.39	0.045	0.055
L3	1.27	1.77	0.050	0.070